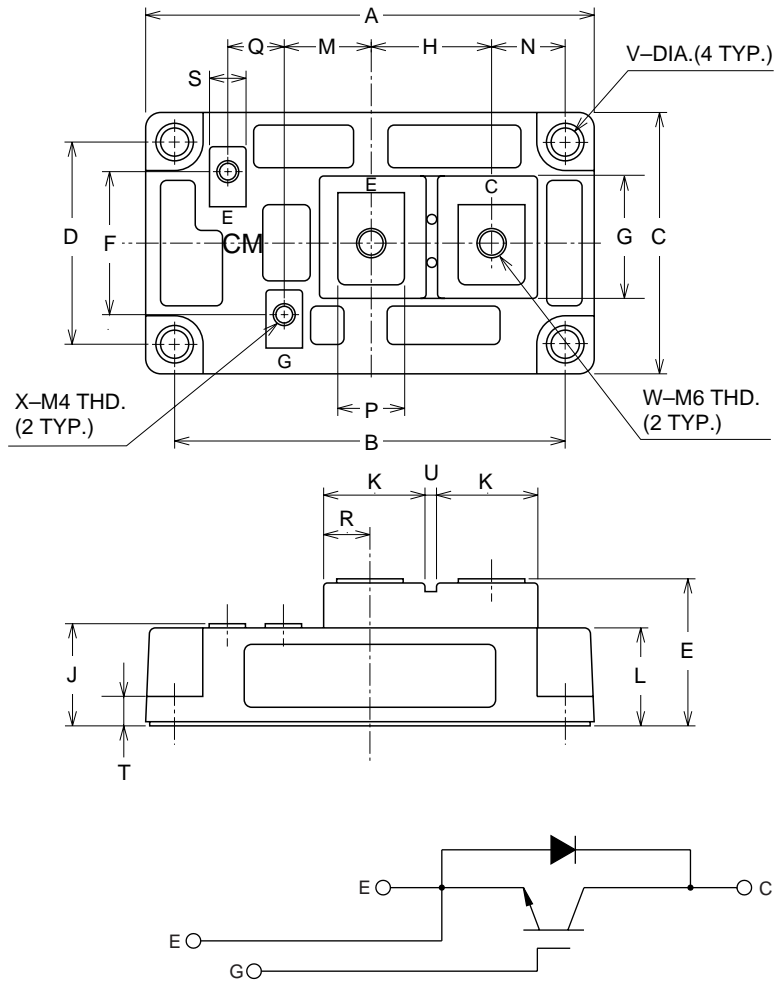


# MITSUBISHI IGBT MODULES

## CM200HA-24H

HIGH POWER SWITCHING USE  
INSULATED TYPE



### Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of one IGBT in a single configuration with a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- High Frequency Operation
- Isolated Baseplate for Easy Heat Sinking

### Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies

### Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e.

CM200HA-24H is a 1200V ( $V_{CES}$ ), 200 Ampere Single IGBT Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	200	24

### Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.21	107.0
B	3.661±0.01	93.0±0.25
C	2.44	62.0
D	1.89±0.01	48.0±0.25
E	1.42 Max.	36.0 Max.
F	1.34	34.0
G	1.18	30.0
H	1.14	29.0
J	0.98 Max.	25.0 Max.
K	0.94	24.0
L	0.93	23.5

Dimensions	Inches	Millimeters
M	0.83	21.0
N	0.69	17.5
P	0.63	16.0
Q	0.51	13.0
R	0.43	11.0
S	0.35	9.0
T	0.28	7.0
U	0.12	3.0
V	0.26 Dia.	Dia. 6.5
W	M6 Metric	M6
X	M4 Metric	M4

## CM200HA-24H

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INSULATED TYPEAbsolute Maximum Ratings,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

	Symbol	Ratings	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{\text{stg}}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	$V_{\text{CES}}$	1200	Volts
Gate-Emitter Voltage (C-E SHORT)	$V_{\text{GES}}$	$\pm 20$	Volts
Collector Current ( $T_c = 25^\circ\text{C}$ )	$I_c$	200	Amperes
Peak Collector Current ( $T_j \leq 150^\circ\text{C}$ )	$I_{\text{CM}}$	400*	Amperes
Emitter Current** ( $T_c = 25^\circ\text{C}$ )	$I_E$	200	Amperes
Peak Emitter Current**	$I_{\text{EM}}$	400*	Amperes
Maximum Collector Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_c$	1500	Watts
Mounting Torque, M6 Main Terminal	–	1.96–2.94	N · m
Mounting Torque, M6 Mounting	–	1.96–2.94	N · m
Mounting Torque, M4 Terminal	–	0.98–1.47	N · m
Weight	–	400	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{\text{iso}}$	2500	Vrms

\* Pulse width and repetition rate should be such that the device junction temperature ( $T_j$ ) does not exceed  $T_{j(\text{max})}$  rating.

\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{\text{CES}}$	$V_{\text{CE}} = V_{\text{CES}}, V_{\text{GE}} = 0\text{V}$	–	–	1.0	mA
Gate Leakage Current	$I_{\text{GES}}$	$V_{\text{GE}} = V_{\text{GES}}, V_{\text{CE}} = 0\text{V}$	–	–	0.5	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_c = 20\text{mA}, V_{\text{CE}} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_c = 200\text{A}, V_{\text{GE}} = 15\text{V}$	–	2.5	3.4**	Volts
		$I_c = 200\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 150^\circ\text{C}$	–	2.25	–	Volts
Total Gate Charge	$Q_G$	$V_{\text{CC}} = 600\text{V}, I_c = 200\text{A}, V_{\text{GE}} = 15\text{V}$	–	1000	–	nC
Emitter-Collector Voltage	$V_{\text{EC}}$	$I_E = 200\text{A}, V_{\text{GE}} = 0\text{V}$	–	–	3.4	Volts

\*\* Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

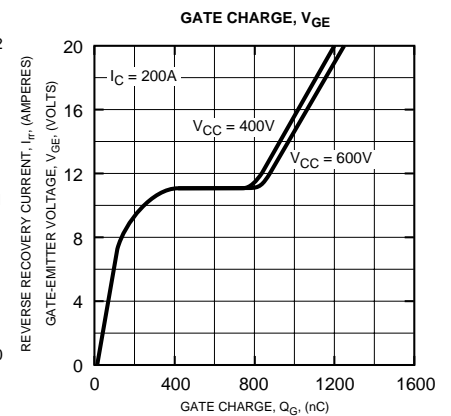
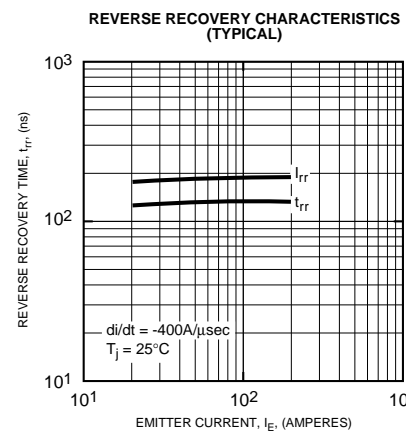
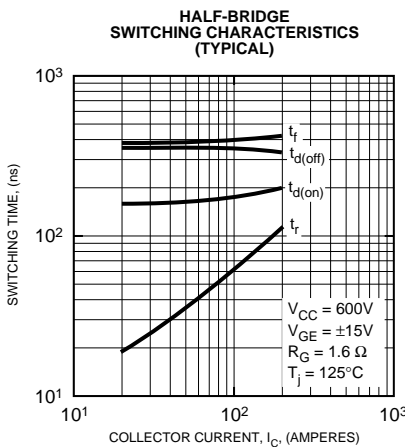
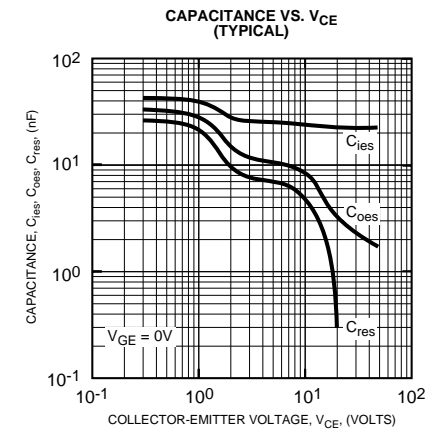
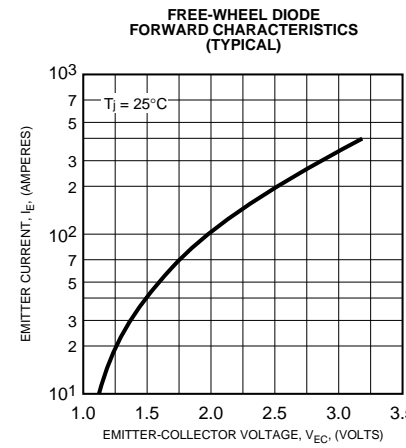
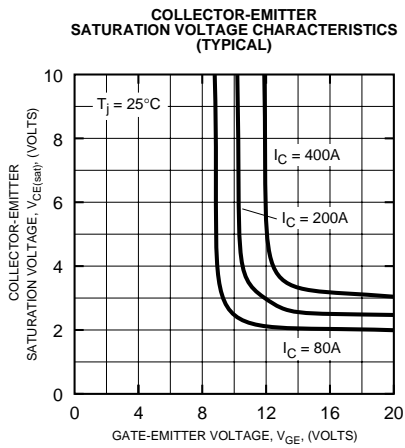
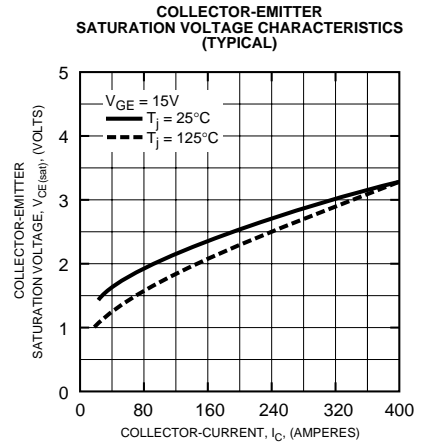
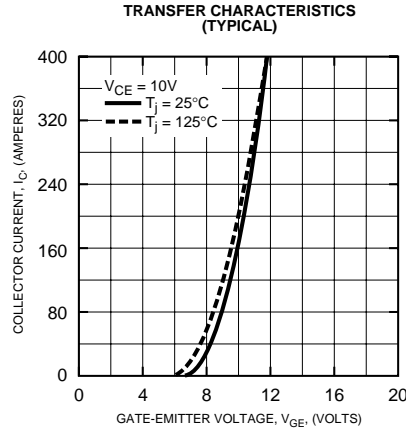
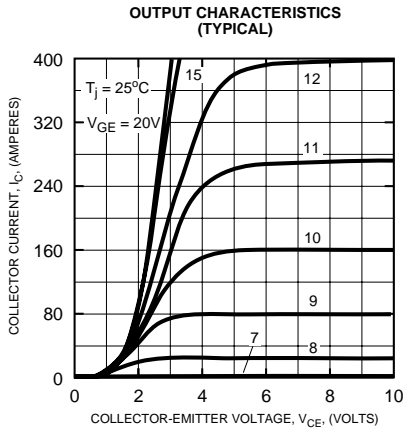
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{\text{ies}}$		–	–	40	nF
Output Capacitance	$C_{\text{oes}}$	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 10\text{V}$	–	–	14	nF
Reverse Transfer Capacitance	$C_{\text{res}}$		–	–	8	nF
Resistive	Turn-on Delay Time	$V_{\text{CC}} = 600\text{V}, I_c = 200\text{A},$ $V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}, R_G = 1.6\Omega$	–	–	250	ns
	Load					
Switching	Turn-off Delay Time	$V_{\text{CC}} = 600\text{V}, I_c = 200\text{A},$ $V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}, R_G = 1.6\Omega$	–	–	300	ns
	Times					
Diode Reverse Recovery Time	$t_{\text{rr}}$	$I_E = 200\text{A}, di_E/dt = -400\text{A}/\mu\text{s}$	–	–	250	ns
Diode Reverse Recovery Charge	$Q_{\text{rr}}$	$I_E = 200\text{A}, di_E/dt = -400\text{A}/\mu\text{s}$	–	1.49	–	$\mu\text{C}$

Thermal and Mechanical Characteristics,  $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per IGBT	–	–	0.085	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per FWDi	–	–	0.18	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	–	–	0.040	$^\circ\text{C}/\text{W}$

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